Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

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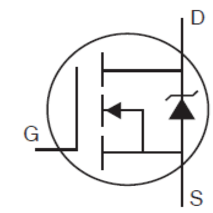
AUTOMOTIVE GRADE

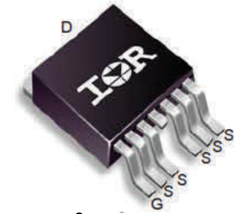
AUIRFSA8409-7P

Features

- Advanced Process Technology
- New Ultra Low On-Resistance
- 175°C Operating Temperature
- Fast Switching
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified *

V_{DSS}		**40V**
$R_{DS(on)}$	typ.	**0.50mΩ**
	max.	**0.69mΩ**
I_D (Silicon Limited)		**523A①**
I_D (Package Limited)		**360A**





D^2PAK-7TP

G	D	S
Gate	Drain	Source

Description

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this design are a 175°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and wide variety of other applications.

Applications

- Electric Power Steering (EPS)
- Battery Switch
- Start/Stop Micro Hybrid
- Heavy Loads
- DC-DC Applications

Base Part Number	Package Type	Standard Pack		Complete Part Number
		Form	Quantity	
AUIRFSA8409-7P	D^2PAK-7TP	Tube	50	AUIRFSA8409-7P
		Tape and Reel Left	800	AUIRFSA8409-7TRL

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (TA) is 25°C, unless otherwise specified.

Symbol	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	523①	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V (Silicon Limited)	370①	
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V (Wire Bond Limited)	360	
I_{DM}	Pulsed Drain Current ②	1440*	
P_D @T_C = 25°C	Maximum Power Dissipation	375	W
	Linear Derating Factor	2.5	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

Avalanche Characteristics

E_{AS} (Thermally Limited)	Single Pulse Avalanche Energy ③	743	mJ
E_{AS} (Thermally Limited)	Single Pulse Avalanche Energy ⑩	1450	
I_{AR}	Avalanche Current ②	See Fig. 14, 15, 24a, 24b	A
E_{AR}	Repetitive Avalanche Energy ②		mJ

*Qualification standards can be found at www.infineon.com

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑨	——	0.4	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑧	——	40	

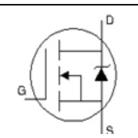
Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	40	——	——	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	0.038	——	V/°C	Reference to 25°C, I_D = 2.0mA②
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	0.50	0.69	mΩ	V_{GS} = 10V, I_D = 100A ⑤
$V_{GS(th)}$	Gate Threshold Voltage	2.2	3.0	3.9	V	V_{DS} = V_{GS}, I_D = 250μA
I_{DSS}	Drain-to-Source Leakage Current	——	——	1.0	μA	V_{DS} = 40V, V_{GS} = 0V
		——	——	150		V_{DS} = 40V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	——	——	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	——	——	-100		V_{GS} = -20V
R_G	Internal Gate Resistance	——	2.3	——	Ω	

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
gfs	Forward Transconductance	180	——	——	S	V_{DS} = 10V, I_D = 100A
Q_g	Total Gate Charge	——	305	460	nC	I_D = 100A
Q_{gs}	Gate-to-Source Charge	——	84	——		V_{DS} = 20V
Q_{gd}	Gate-to-Drain ("Miller") Charge	——	96	——		V_{GS} = 10V ⑤
Q_{sync}	Total Gate Charge Sync. (Q_g - Q_{gd})	——	209	——		
$t_{d(on)}$	Turn-On Delay Time	——	21	——	ns	V_{DD} = 20V
t_r	Rise Time	——	94	——		I_D = 100A
$t_{d(off)}$	Turn-Off Delay Time	——	150	——		R_G = 2.7Ω
t_f	Fall Time	——	90	——		V_{GS} = 10V ⑤
C_{iss}	Input Capacitance	——	13975	——	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	——	2140	——		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	——	1438	——		ƒ = 1.0 MHz
C_{oss} eff. (ER)	Effective Output Capacitance (Energy Related) ⑦	——	2620	——		V_{GS} = 0V, V_{DS} = 0V to 32V ⑦
C_{oss} eff. (TR)	Effective Output Capacitance (Time Related)⑥	——	3306	——		V_{GS} = 0V, V_{DS} = 0V to 32V ⑥

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	——	523①	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ②	——	——	1440*	A	
V_{SD}	Diode Forward Voltage	——	0.8	1.3	V	T_J = 25°C, I_S = 100A, V_{GS} = 0V ⑤
dv/dt	Peak Diode Recovery ④	——	3.1	——	V/ns	T_J = 175°C, I_S = 100A, V_{GS} = 40V
t_{rr}	Reverse Recovery Time	——	59	——	ns	T_J = 25°C; V_R = 34V, I_F = 100A, di/dt = 100A/μs⑤
		——	60	——		T_J = 125°C
Q_{rr}	Reverse Recovery Charge	——	96	——	nC	T_J = 25°C
		——	98	——		T_J = 125°C
I_{RRM}	Reverse Recovery Current	——	2.7	——	A	T_J = 25°C

Notes:

① Calculated continuous current based on maximum allowable junction temperature. Bond wire current limit is 360A. Note that current limitations arising from heating of the device leads may occur with some lead mounting arrangements. (Refer to AN-1140)

② Repetitive rating; pulse width limited by max. junction temperature.

③ Limited by T_{Jmax}, starting T_J = 25°C, L = 0.15mH R_G = 50Ω, I_{AS} = 100A, V_{GS} =10V.

④ I_{SD} ≤ 100A, di/dt ≤ 1070A/μs, V_{DD} ≤ $V_{(BR)DSS}$, T_J ≤ 175°C.

⑤ Pulse width ≤ 400μs; duty cycle ≤ 2%.

⑥ C_{oss} eff. (TR) is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

⑦ C_{oss} eff. (ER) is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS}.

⑧ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

⑨ R_θ is measured at T_J approximately 90°C.

⑩ Limited by T_{Jmax}, starting T_J = 25°C, L = 1mH, R_G = 50Ω, I_{AS} = 53A, V_{GS} =10V.

* Pulse drain current is limited to 1440A by source bonding technology

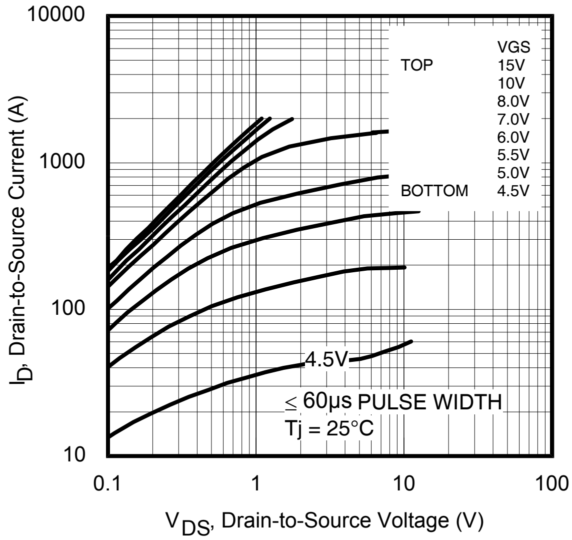


Fig. 1 Typical Output Characteristics

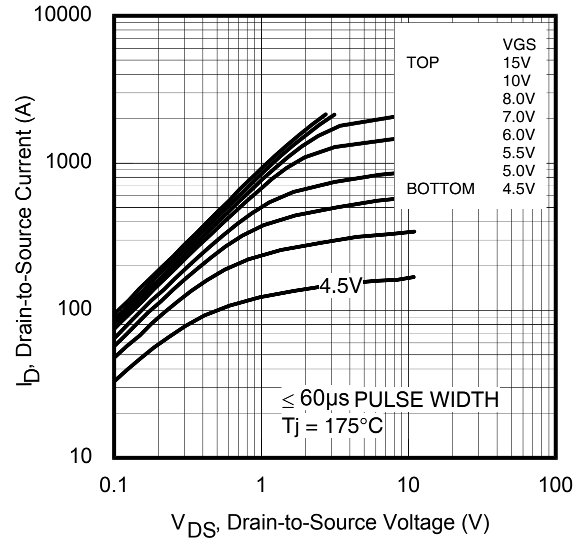


Fig. 2 Typical Output Characteristics

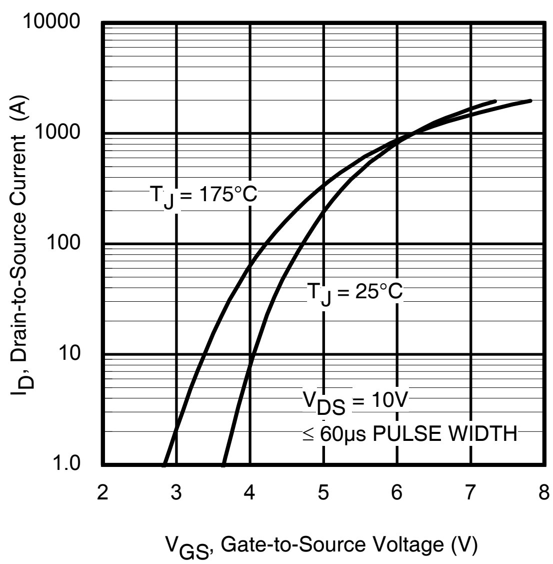


Fig. 3 Typical Transfer Characteristics

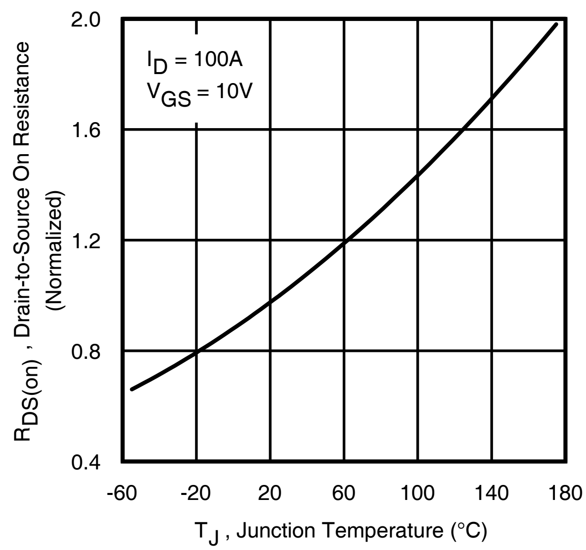


Fig. 4 Normalized On-Resistance vs. Temperature

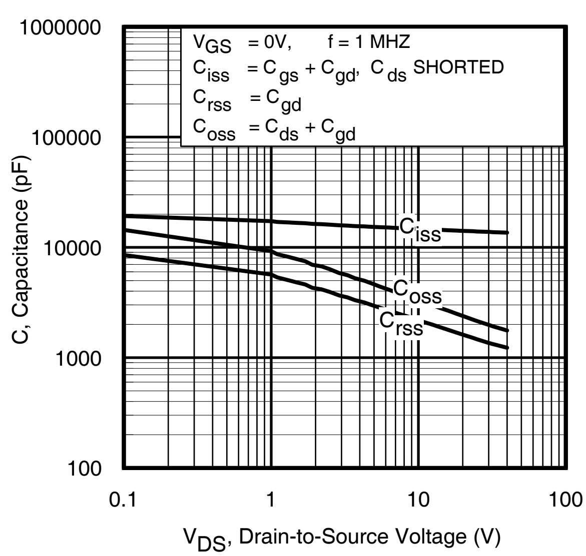


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

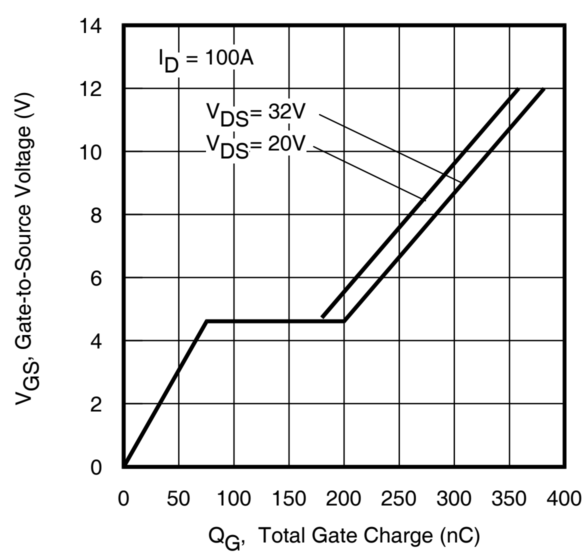


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

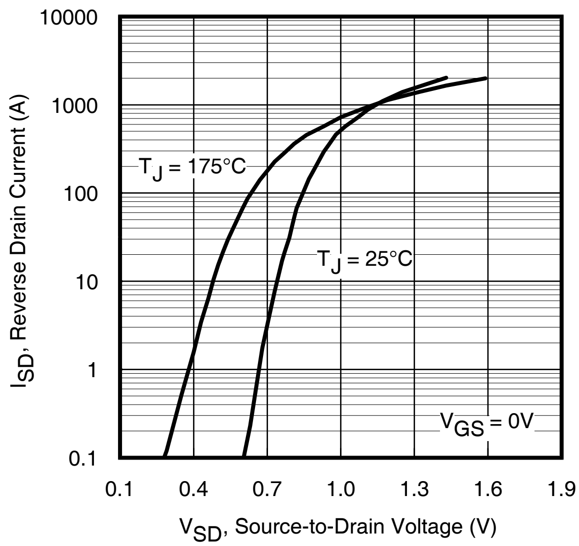


Fig. 7 Typical Source-to-Drain Diode Forward Voltage

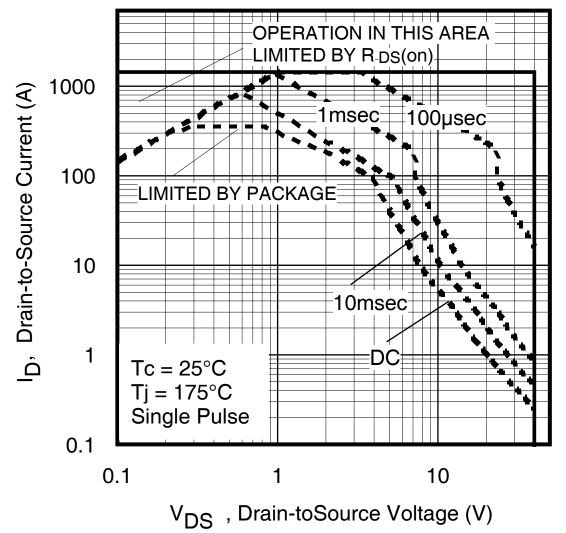


Fig 8. Maximum Safe Operating Area

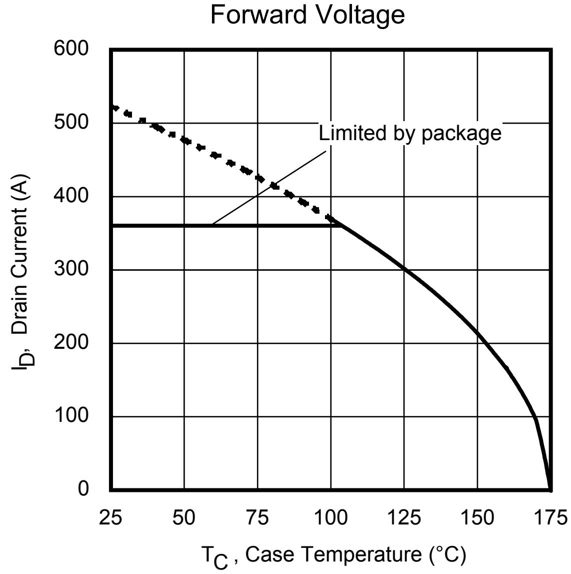


Fig 9. Maximum Drain Current vs. Case Temperature

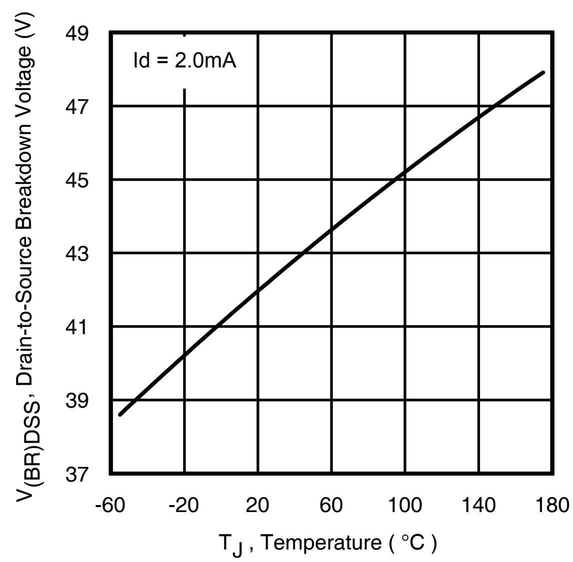


Fig 10. Drain-to-Source Breakdown Voltage

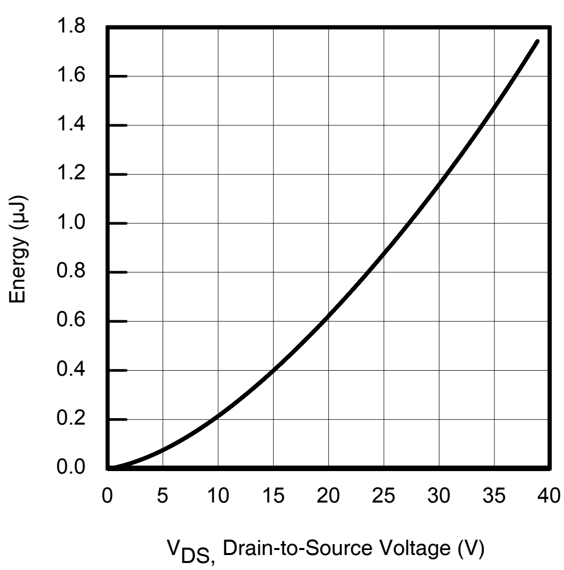


Fig 11. Typical Coss Stored Energy

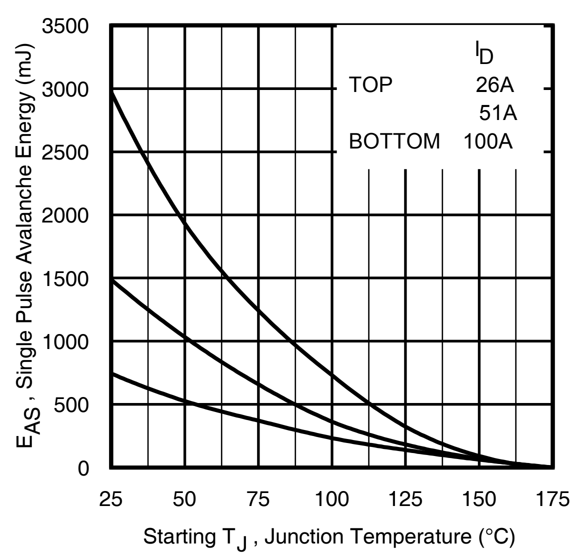


Fig 12. Maximum Avalanche Energy vs. Drain Current

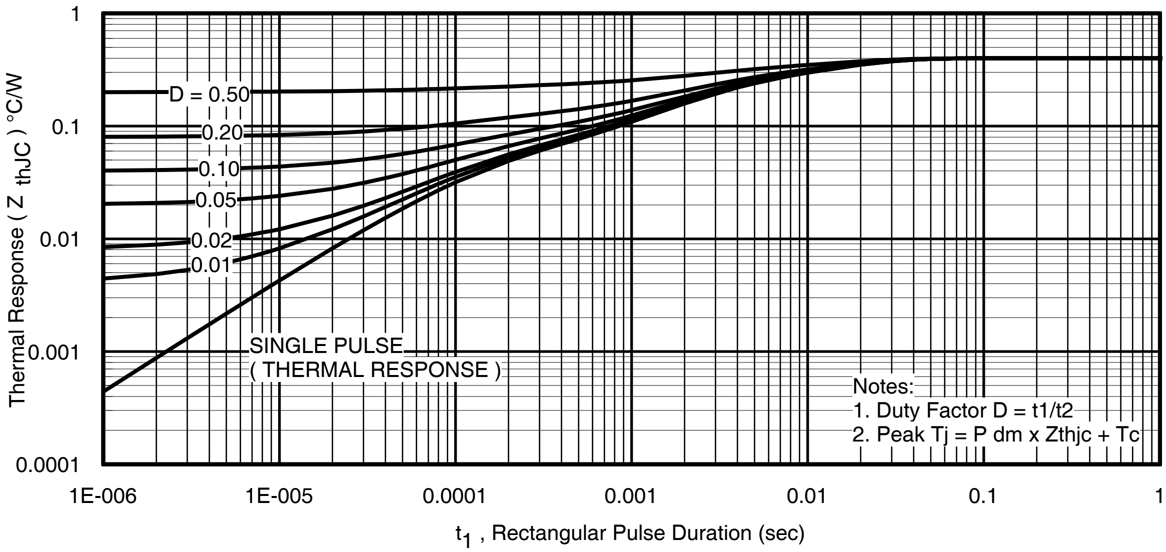


Fig 13. Maximum Effective Transient Thermal Impedance, Junction-to-Case

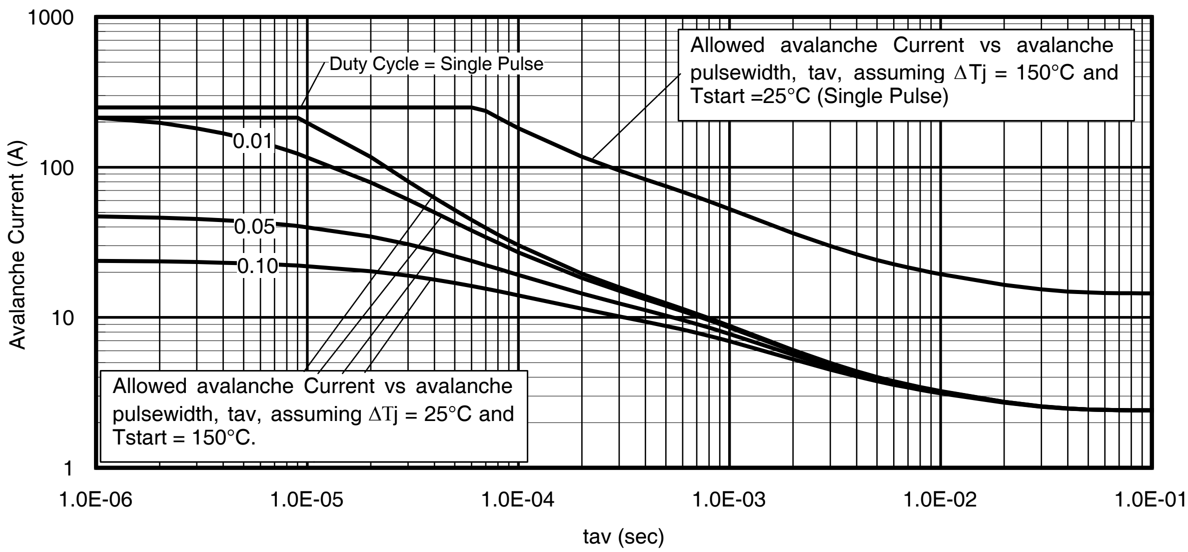


Fig 14. Avalanche Current vs. Pulse width

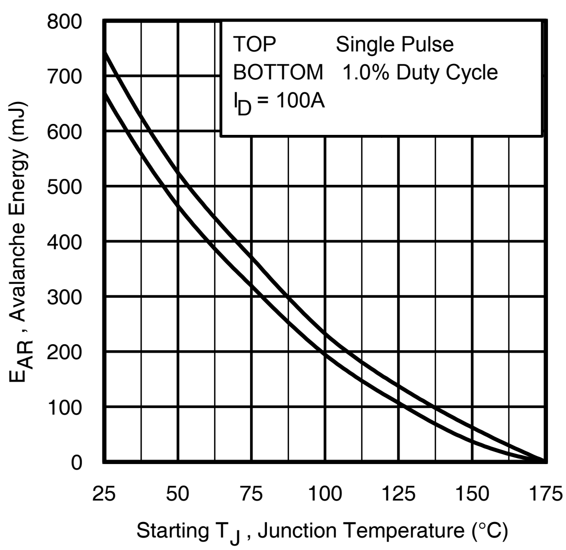


Fig 15. Maximum Avalanche Energy vs. Temperature

Notes on Repetitive Avalanche Curves , Figures 14, 15:
(For further info, see AN-1005 at www.irf.com)

1. Avalanche failures assumption:
   Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax}. This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 24a, 24b.
4. $P_{D\ (ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 13, 14).
   t_{av} = Average time in avalanche.
   D = Duty cycle in avalanche = $t_{av} \cdot f$
   $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13.

$$P_{D\ (ave)} = 1/2\ (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$
$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$
$$E_{AS\ (AR)} = P_{D\ (ave)} \cdot t_{av}$$

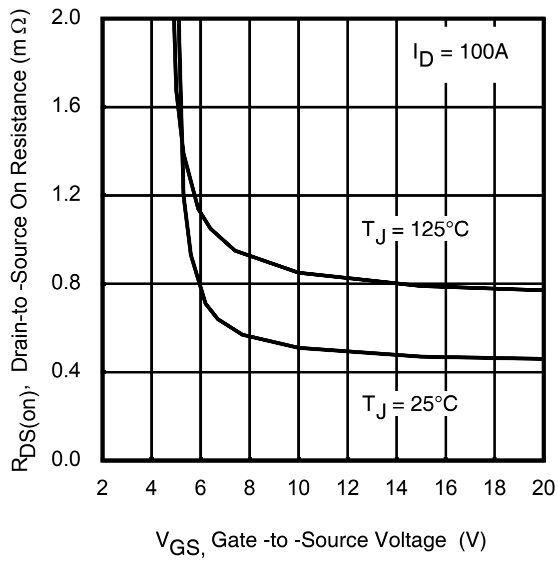


Fig 16. Typical On-Resistance vs. Gate Voltage

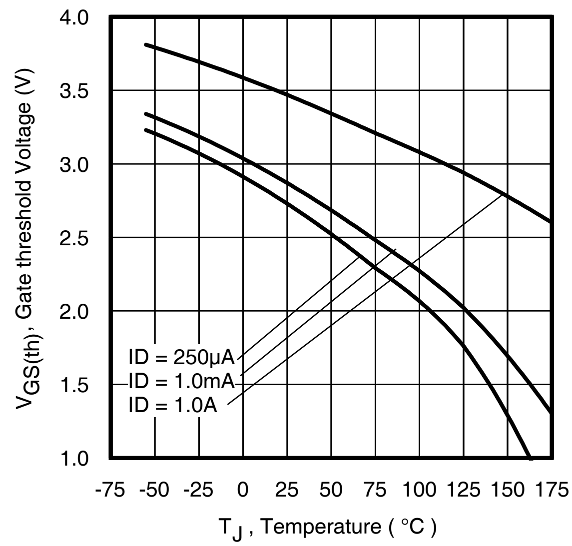


Fig 17. Threshold Voltage vs. Temperature

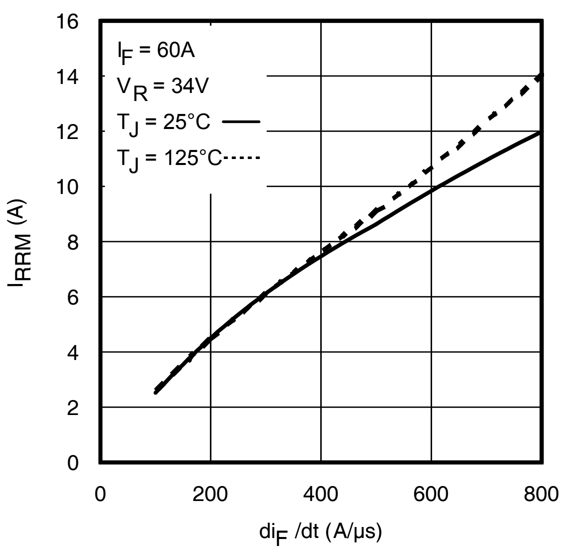


Fig. 18 - Typical Recovery Current vs. dif/dt

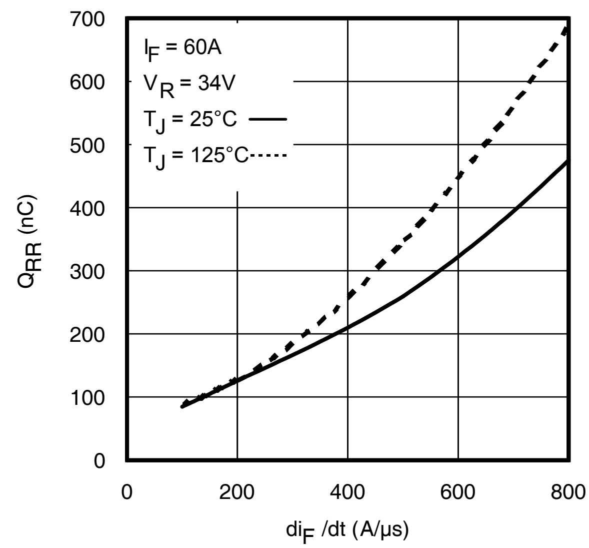


Fig. 19 - Typical Stored Charge vs. dif/dt

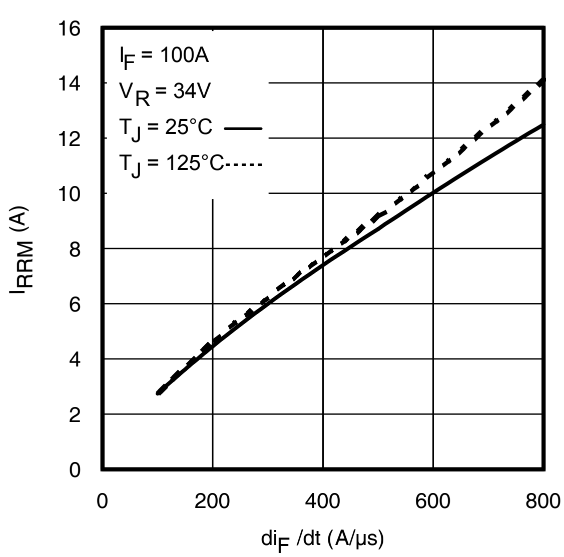


Fig. 20 - Typical Recovery Current vs. dif/dt

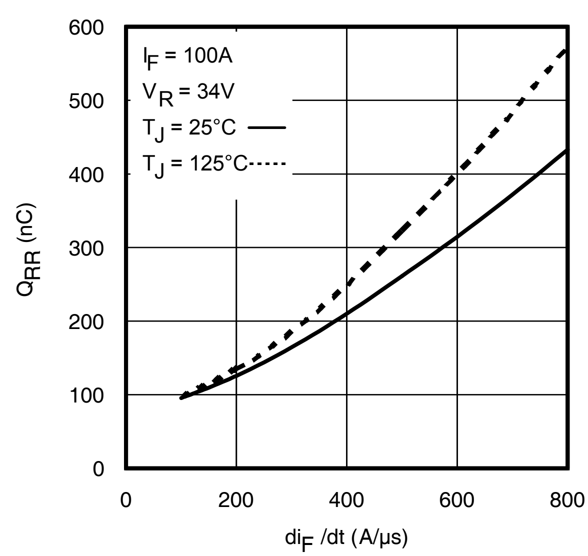


Fig. 21 - Typical Stored Charge vs. dif/dt

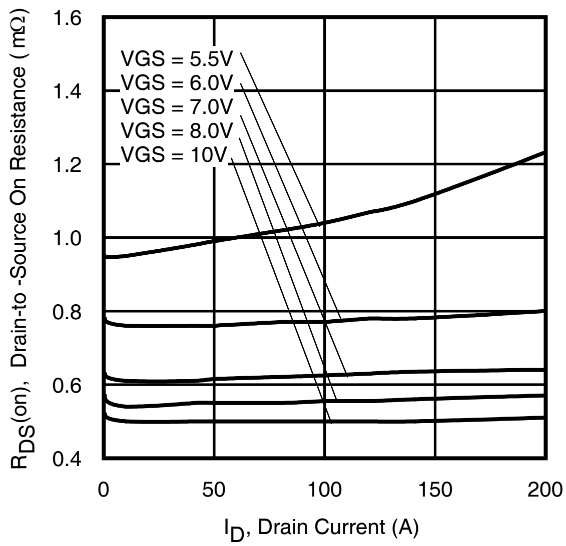


Fig 22. Typical On-Resistance vs. Drain Current

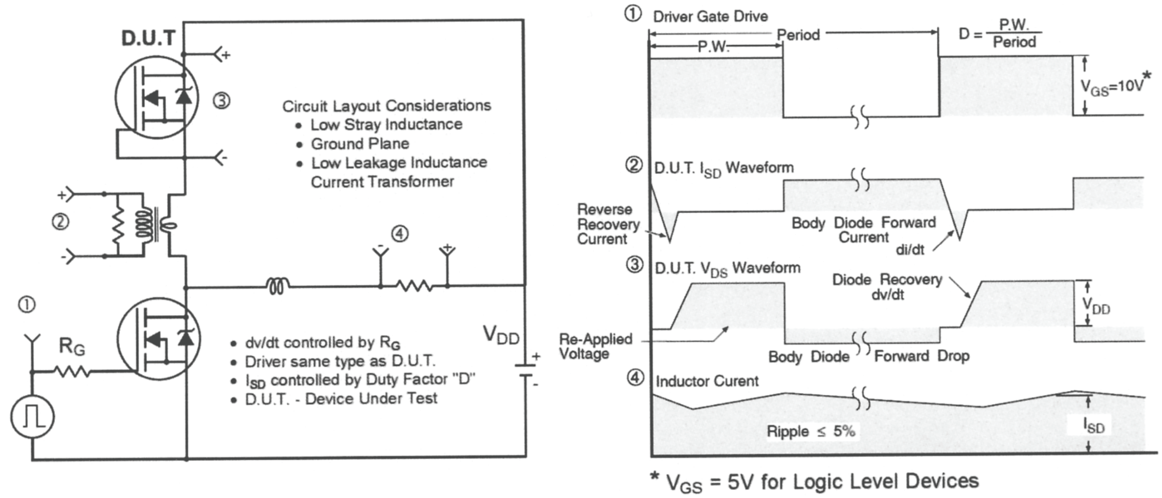


Fig 23. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

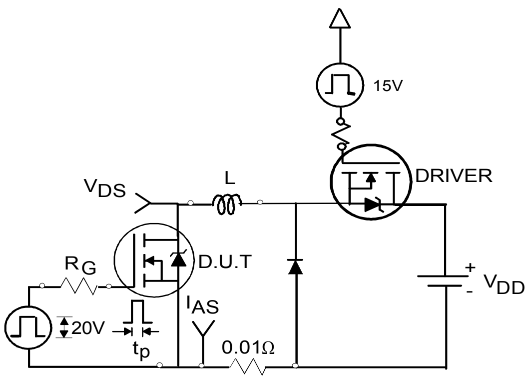


Fig 24a. Unclamped Inductive Test Circuit

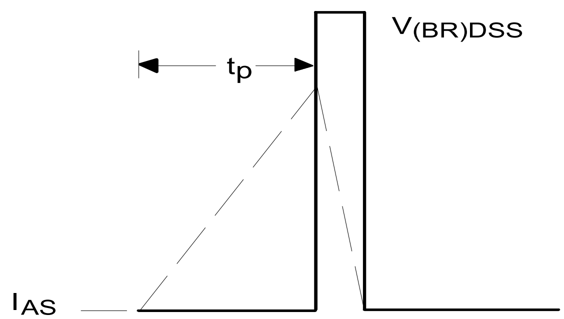


Fig 24b. Unclamped Inductive Waveforms

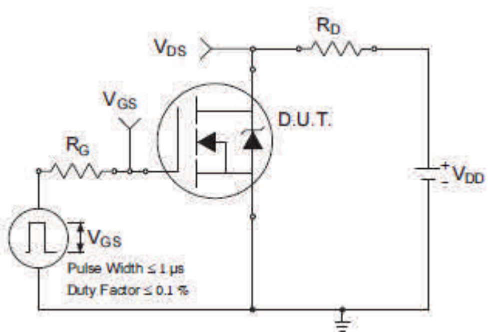


Fig 25a. Switching Time Test Circuit

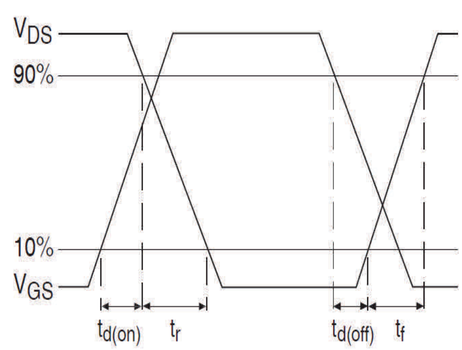


Fig 25b. Switching Time Waveforms

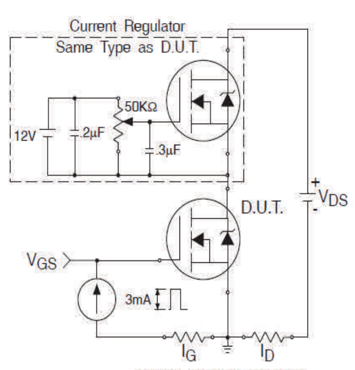


Fig 26a. Gate Charge Test Circuit

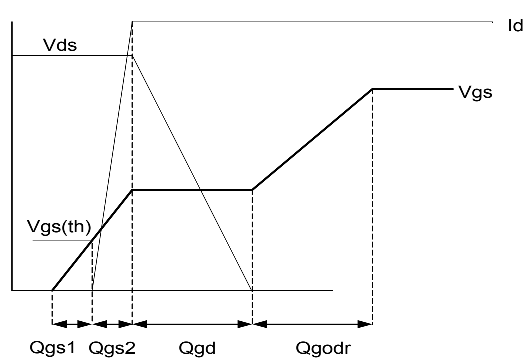
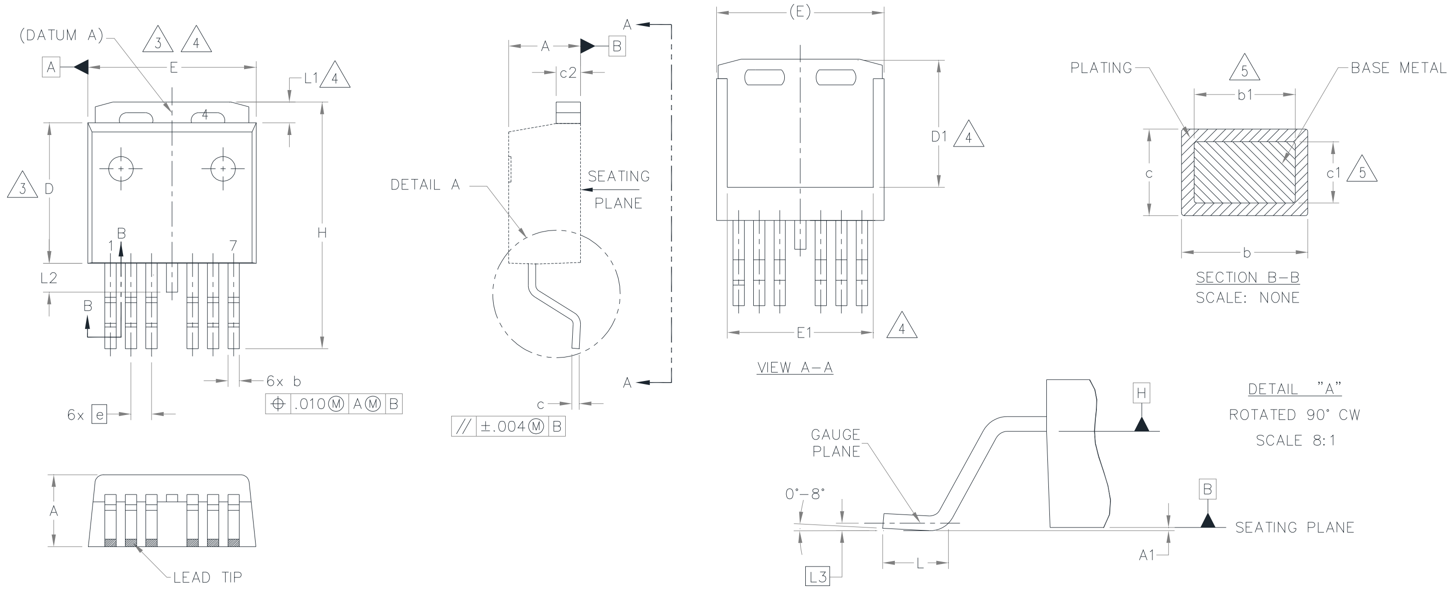


Fig 26b. Gate Charge Waveform

D²PAK-7TP Package Outline (Dimensions are shown in millimeters (inches))



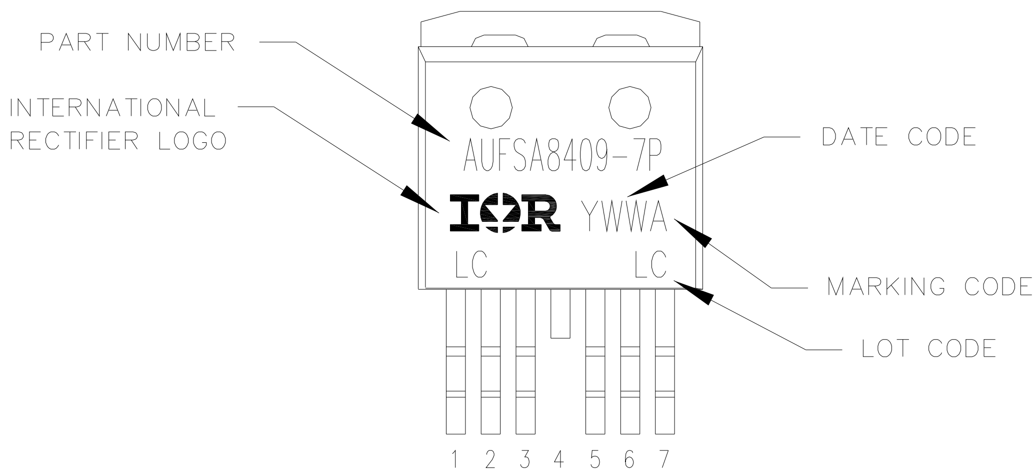
SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	–	0.254	–	.010	
b	0.51	0.91	.020	.036	
b1	0.51	0.81	.020	.032	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	7.42	.270	.292	4
E	9.65	10.54	.380	.415	3,4
E1	8.00	9.00	.315	.354	4
e	1.27 BSC		.050 BSC		
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	–	1.68	–	.066	4
L2	–	1.78	–	.070	
L3	0.25 BSC		.010 BSC		

NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M–1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
4. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
7. CONTROLLING DIMENSION: INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO–263CB. EXCEPT FOR DIMS. E, E1 & D1.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

D²PAK-7TP Part Marking Information

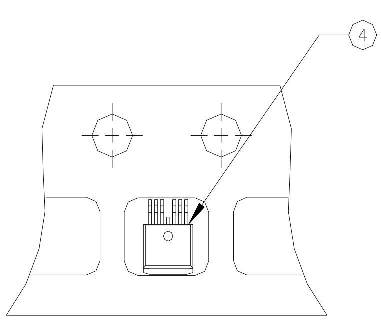


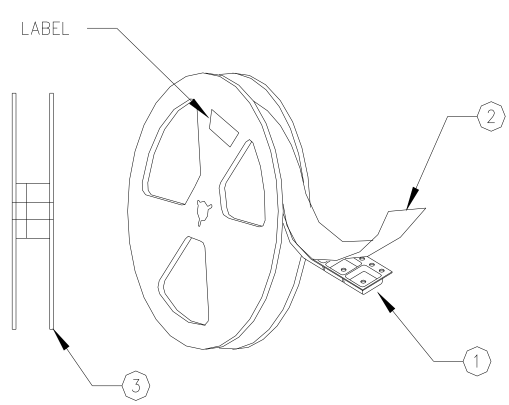
D²PAK-7TP Tape and Reel

NOTES, TAPE & REEL, LABELLING:

1. TAPE AND REEL.
   - 1.1 REEL SIZE 13 INCH DIAMETER.
   - 1.2 EACH REEL CONTAINING 800 DEVICES.
   - 1.3 THERE SHALL BE A MINIMUM OF 42 SEALED POCKETS CONTAINED IN THE LEADER AND A MINIMUM OF 15 SEALED POCKETS IN THE TRAILER.
   - 1.4 PEEL STRENGTH MUST CONFORM TO THE SPEC. NO. 71-9667.
   - 1.5 PART ORIENTATION SHALL BE AS SHOWN BELOW.
   - 1.6 REEL MAY CONTAIN A MAXIMUM OF TWO UNIQUE LOT CODE/DATE CODE COMBINATIONS. REWORKED REELS MAY CONTAIN A MAXIMUM OF THREE UNIQUE LOT CODE/DATE CODE COMBINATIONS. HOWEVER, THE LOT CODES AND DATE CODES WITH THEIR RESPECTIVE QUANTITIES SHALL APPEAR ON THE BAR CODE LABEL FOR THE AFFECTED REEL.

2. LABELLING (REEL AND SHIPPING BAG).
   - 2.1 CUST. PART NUMBER (BAR CODE): IRFXXXXSTRL-7P
   - 2.2 CUST. PART NUMBER (TEXT CODE): IRFXXXXSTRL-7P
   - 2.3 I.R. PART NUMBER: IRFXXXXSTRL-7P
   - 2.4 QUANTITY:
   - 2.5 VENDOR CODE: IR
   - 2.6 LOT CODE:
   - 2.7 DATE CODE:





Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Qualification Information†

Qualification Level		Automotive (per AEC-Q101)	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
		D^2PAK-7TP	MSL1
ESD	Human Body Model	Class H3A (± 8000V) † AEC-Q101-001	
	Charged Device Model	Class C5 (± 2000V) † AEC-Q101-005	
RoHS Compliant		Yes	

† Highest passing voltage.

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